

# HD1530FX

High Voltage NPN Power Transistor for High Definition and New Super-Slim CRT Display

### Features

- STATE-OF-THE-ART TECHNOLOGY: DIFFUSED COLLECTOR "ENHANCED GENERATION" EHVS1
- WIDER RANGE OF OPTIMUM DRIVE CONDITIONS
- LESS SENSITIVE TO OPERATING TEMPERATURE VARIATION
- FULLY INSULATED POWER PACKAGE WHICH IS U.L COMPLIANT

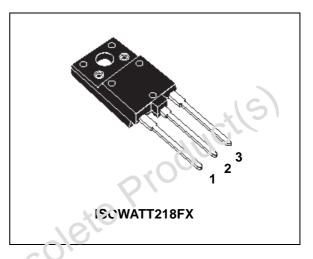
### **Applications**

 HORIZONTAL DEFLECTION OUTPUT FOR DIGITAL TV, HDTV, AND HIGH -END MONITORS

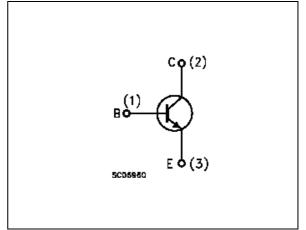
### Description

The device uses a Diffused Collector in Planar technology which adopts "Enhanced High Voltage Structure" (EHVS1) that was developed to fit High-Definition CRT displays.

The new HD product series features improved silicon efficiency, bringing updated performance to Horizontal Derlection output stages.



# Internal Schematic Diagram



### **Order Codes**

Part Number	Marking	Package	Packing
HD1530FX	HD1530FX	ISOWATT218FX	TUBE

August 2	2005
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### **Absolute Maximum Ratings** 1

	Absolute maximum Natingsh				
Symbol	Parameter	Value	Unit		
V <sub>CES</sub>	Collector-Emitter Voltage (V <sub>BE</sub> = 0)	1500	V		
V <sub>CEO</sub>	Collector-Emitter Voltage (I <sub>B</sub> = 0)	700	V		
V <sub>EBO</sub>	Emitte-Base Voltage ( $I_C = 0$ )	10	V		
۱ <sub>C</sub>	Collector Current	26	Α		
I <sub>CM</sub>	Collector Peak Current (t <sub>P</sub> < 5ms)	40	А		
Ι <sub>Β</sub>	Base Current	10	Α		
I <sub>BM</sub>	Base Peak Current (t <sub>P</sub> < 5ms)20				
P <sub>TOT</sub>	Total dissipation at $T_c = 25^{\circ}C$ 70		W		
V <sub>ins</sub>	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	2500	V		
T <sub>STG</sub>	Storage Temperature	. 65 to 150	°C		
ТJ	Max. Operating Junction Temperature	150	°C		
1.1 Thermal Data					
Symbol	Parameter	Value	Unit		

#### Table 1. **Absolute Maximum Ratingsn**

#### 1.1 **Thermal Data**

#### Table 2. **Thermal Data**

	Symbol	Parameter		Value	Unit	
Ē	R <sub>thJC</sub>	Thermal Resistance Junction Case	Мах	1.8	°C/W	
L		CIC	ł			
		du				
		O <sup>(O)</sup>				
		. C. 1				
		SIG				
	cO'					
$\cap$	$\mathbf{o}$					

# 2 Electrical Characteristics

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I <sub>CES</sub>	Collector Cut-off Current (V <sub>BE</sub> = 0)	$V_{CE} = 1500V$ $V_{CE} = 1500V$ $T_{C} = 125^{\circ}C$			0.2 2	mA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5V			10	μA
V <sub>CEO(sus)</sub> Note: 1	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 10mA	700		. 0	v
V <sub>EBO</sub>	Emitter-Base Voltage	I <sub>E</sub> = 10mA	10		11	V
V <sub>CE(sat)</sub> Note: 1	Collector-Emitter saturation Voltage	I <sub>C</sub> = 13A I <sub>B</sub> = 3.25A		90	2	V
V <sub>BE(sat)</sub> Note: 1	Base-Emitter saturation Voltage	I <sub>C</sub> = 13A I <sub>B</sub> = 3.25A	61	1	1.5	V
h <sub>FE</sub>	DC Current Gain	$I_{C} = 1A$ $V_{CE} = 5V$ $I_{C} = 13A$ $V_{C'E} = 5v'$	5.5	30	9	
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	$I_{C} = 12A$ $I_{B(on)} = 1.4$ $I_{B(off)} = -6A$		3.2 230		μs ns
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	$f_{C} = 12A$ $f_{h} = 48KHz$ $I_{B(on)} = 2A$ $I_{B(off)} = -6.7A$		2.8 200		μs ns
t <sub>s</sub> t <sub>f</sub>	INDUCTIVE LOAD Storage Time Fall Time	$I_{C} = 6.5A$ $f_{h} = 100 \text{KHz}$ $I_{B(on)} = 0.8A$ $I_{B(off)} = -4.5A$		1.4 100		μs ns

Table 3.Electrical Characteristics ( $T_{CASE} = 25^{\circ}C$ ; unless otherwise specified)

Note: 1 Pu's a duration =  $300 \,\mu$ s, duty cycle  $\leq 1.5\%$ .



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# 3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

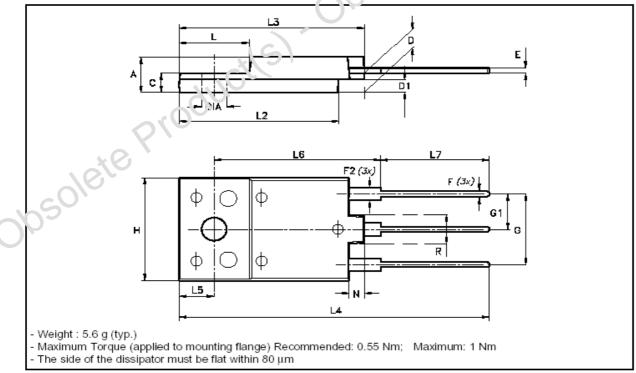
obsolete Product(s). Obsolete Product(s)



DIM.		mm			inch	
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	5.30		5.70	0.209		0.224
С	2.80		3.20	0.110		0.126
D	3.10		3.50	0.122		0.138
D1	1.80		2.20	0.071		0.087
E	0.80		1.10	0.031		0.043
F	0.65		0.95	0.026		0.037
F2	1.80		2.20	0.071		0.087
G	10.30		11.50	0.406		0.453
G1		5.45			0.215	
Н	15.30		15.70	0.602		0.618
L	9.0		10.20	0.354		0.492
L2	22.80		23.20	0.898		0.91',
L3	26.30		26.70	1.035		1.051
L4	43.20		44.40	1.701		1.748
L5	4.30		4.70	0.169		0.185
L6	24.30		24.70	0.957	~~0	0.972
L7	14.60		15.00	0.575		0.591
Ν	1.80		2.20	0.071		0.087
R	3.80		4.20	0 151		0.165
DIA	3.40		3.80	6 134		0.150

Table 4. ISOWATT218FX Mechanical Data

### Figure 1. ISOWATT218FX Drawing





# 4 Revision History

	Date	Revision	Changes
	05-July-2005	1	Initial release.
	25-July-2005	2	New Template, no content change
	19-Aug-2005	3	New ECOPACK® label
0050	etepro	duct	New ECOPACK® label



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